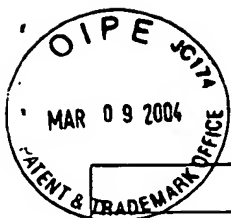


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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117588		APPLICATION NO. 10/689,990	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Yoshikazu KASUYA			
				FILING DATE October 22, 2003			
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EXAMINER			DATE CONSIDERED		
V. Gershon			05/04/04		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

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